

Specifications for N on P Silicon Epi-DSP Wafers		
Substrate Specifications:		
1	Material	Silicon
2	Diameter	150±0.2mm/0.5mm
3	Wafer Orientation	<100>±1°
4	Growth	CZ
5	Type	p-type (Boron)
6	Thickness	0.6 μm
7	Resistivity	8-12 Ω.cm
8	Radial Resistivity Variation	10% (10 mm edge exclusion)
9	Oxygen Content	10.2-15.8 ppma (ASTM F121-83)
10	Carbon Content	1 ppma (ASTM F 123-83)
11	Primary Flat	Orientation <110>±1°; length=57.5mm±2.5mm; Semi Std.
12	Edge Profile	Semi Std M1.8-89
Epi Wafer Specifications:		
1	LFPD	0.6μ
2	Bow	<25μ
3	Warp	<25μ
4	TTV	<6μ
5	TIR	<3μ
Epi Layer Specifications		
6	Epi-Layer Thickness	a-Si 4.0±0.5 μm SiO2 3±0.2 μm
7	Dopant	Phosphorous
8	Resistivity	3-5 Ω.cm
9	Radial Resistivity Variation	10%
10	Point Defects	Semi Standard
11	Particulate	<10 of size >0.5μ